

Model Comparison

Model	VRRMVDRM(V)	ITAVIFAV(A)
CDD253N08	800	310
CDD253N12	1200	310
CDD253N14	1400	310
CDD253N16	1600	310
CDD253N18	1800	310
CDD253N20	2000	310
CDD253N22	2200	310

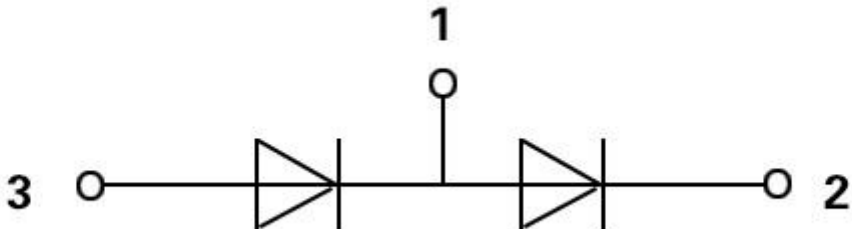
Features / Advantages

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

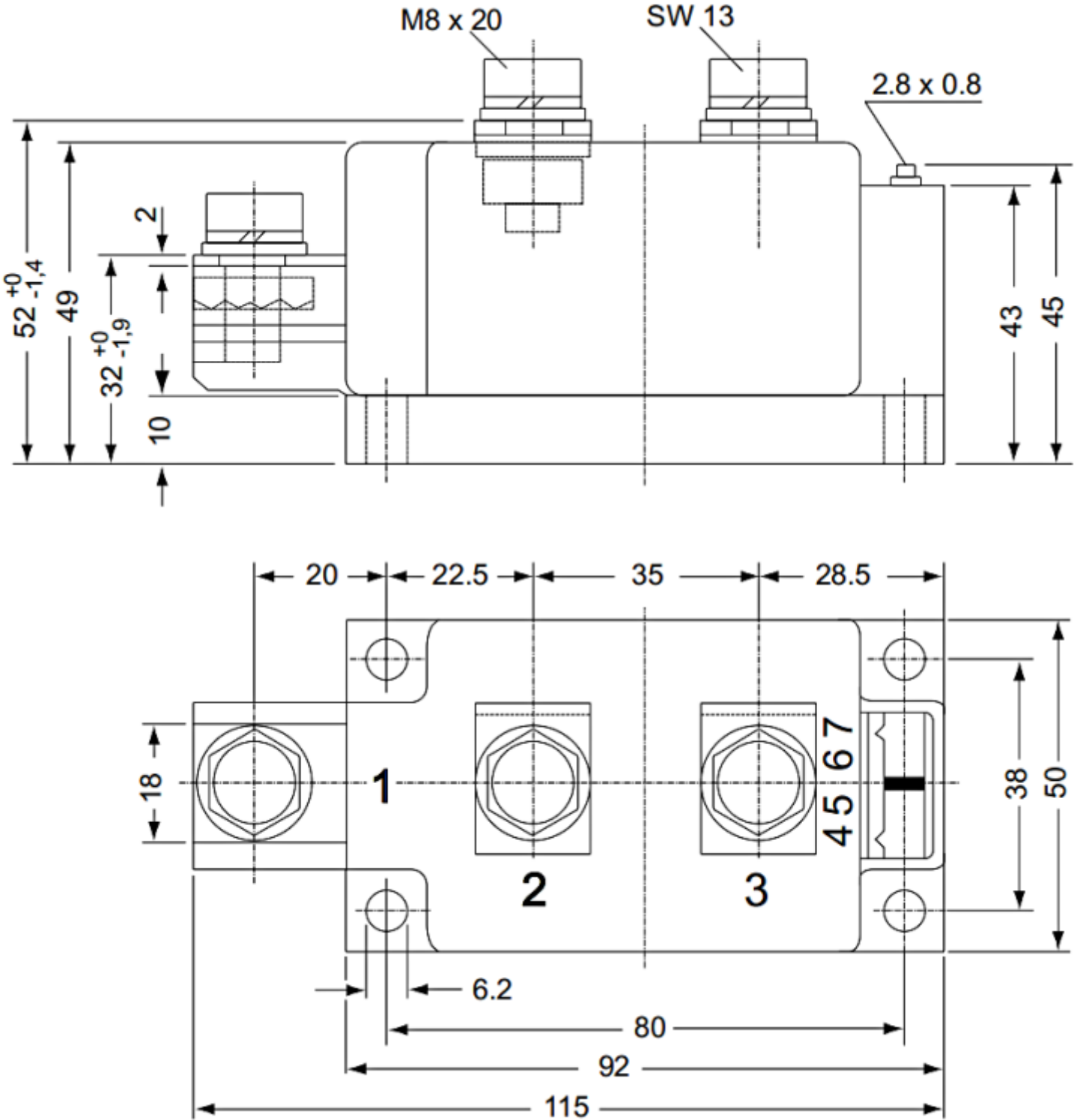
Applications

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Internal Circuit



Package Dimension
Dimensions in Millimeters



Parameters

Parametrics	CDD253N08~22
V_{DRM} V_{RRM}	800~2200V
I_{TAV} I_{FAV} @TC	310A
T_{C}	100°C
I_{TSM} I_{FSM} @10ms, T_{vj} max	10500A
$V_{\text{(FM)}}$ @ T_{vj} max	0.80V
Package style Outline drawings	XTD